PROCESS CP370

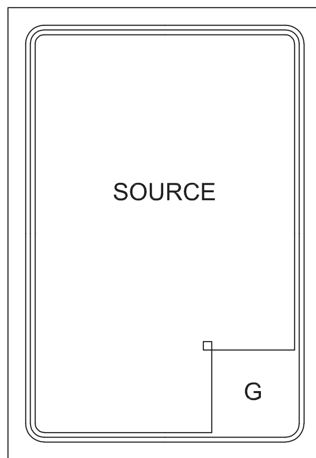
N-Channel MOSFET

Enhancement-Mode MOSFET Chip

PROCESS DETAILS

Die Size	39 x 27 MILS
Die Thickness	7.5 MILS
Gate Bonding Pad Area	6.5 x 6.5 MILS
Source Bonding Pad Area	30 x 20 MILS
Top Side Metalization	Al - 40,000Å
Back Side Metalization	Ti/Ni/Ag - 1,000Å/3,000Å/10,000Å

GEOMETRY

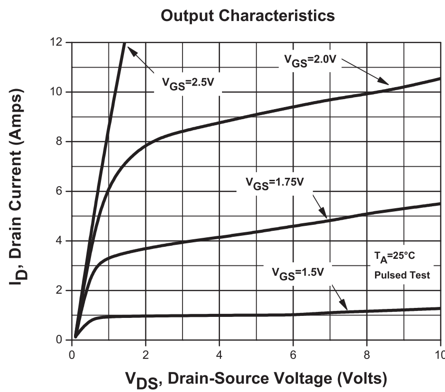


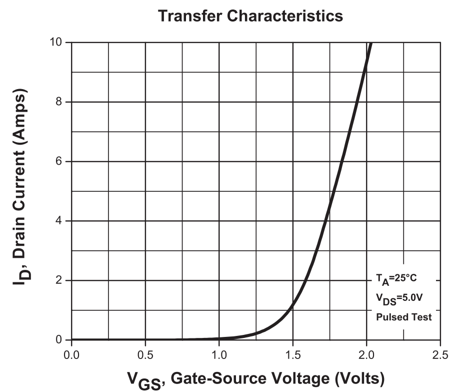
GROSS DIE PER 8 INCH WAFER
43,500

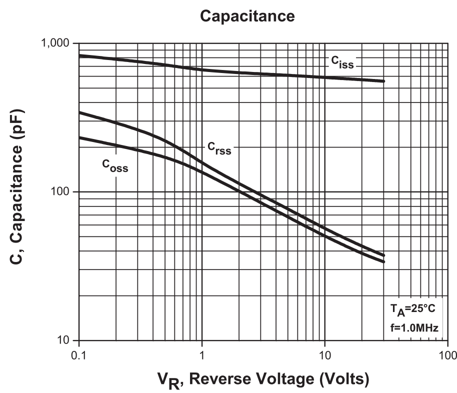
PRINCIPAL DEVICE TYPE
CXDM3069N

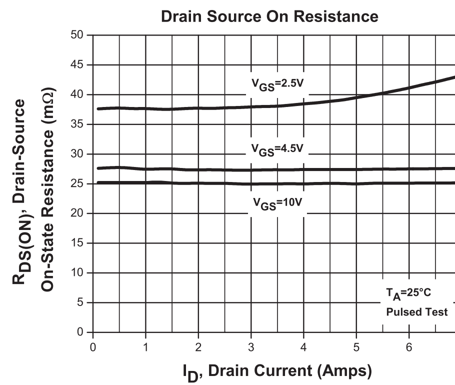
PROCESS CP370

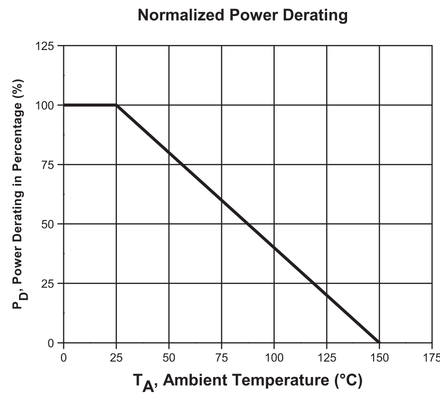
Typical Electrical Characteristics











R0 (10-December 2012)